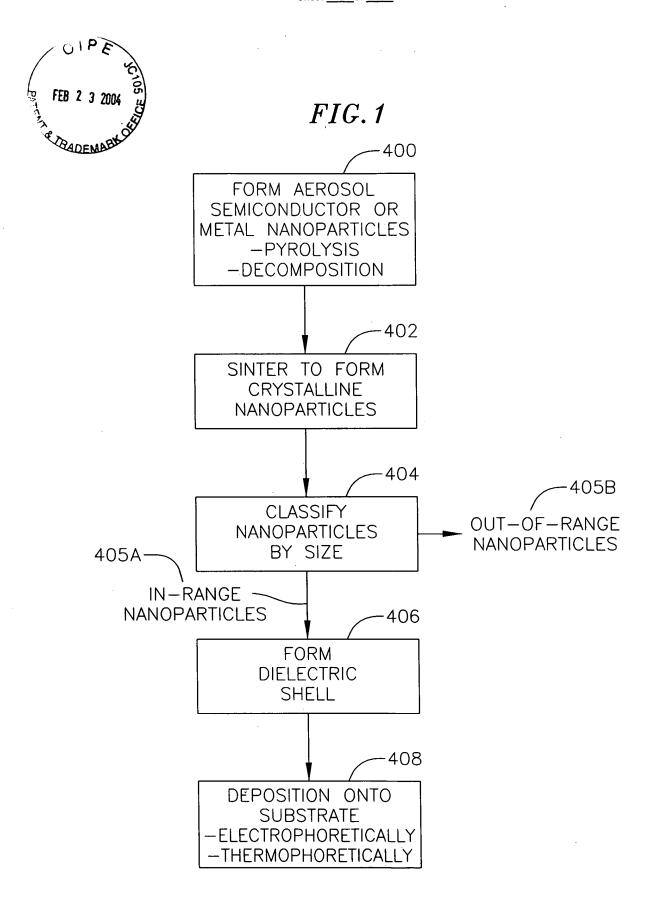
Title: AEROSOL PROCESS FOR FABRICATING DISCONTINUOUS FLOATING GATE MICROELECTRONIC DEVICES

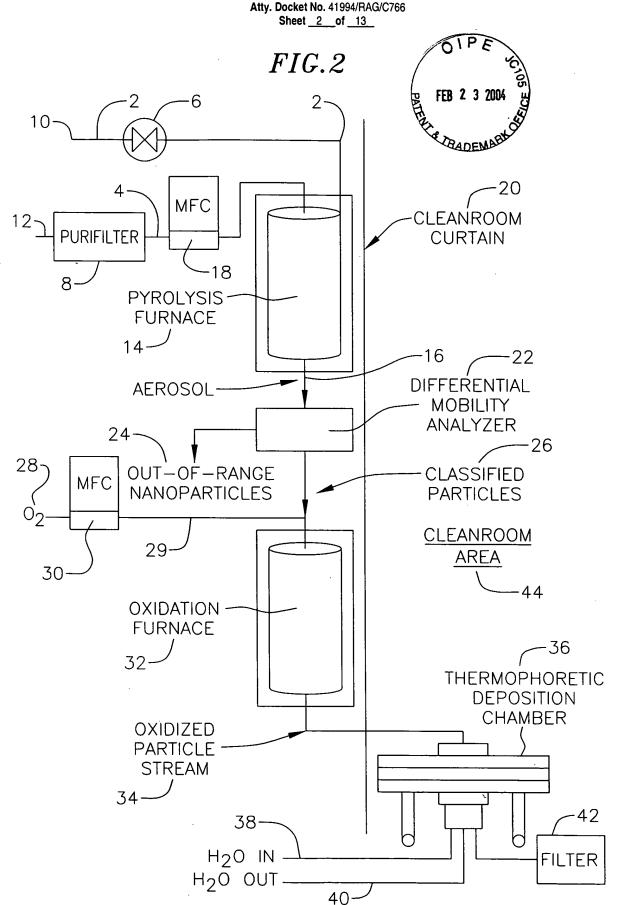
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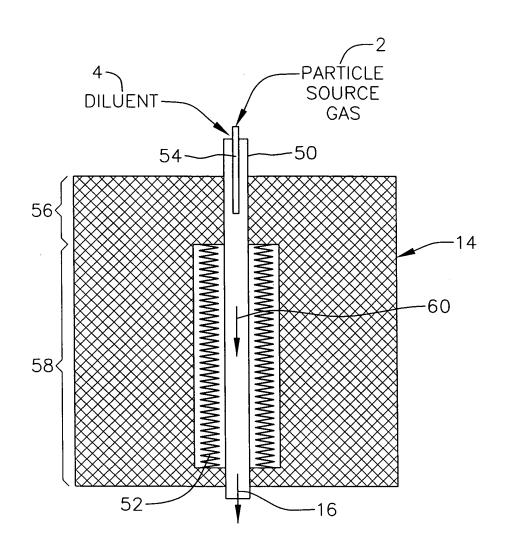


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FIG.3

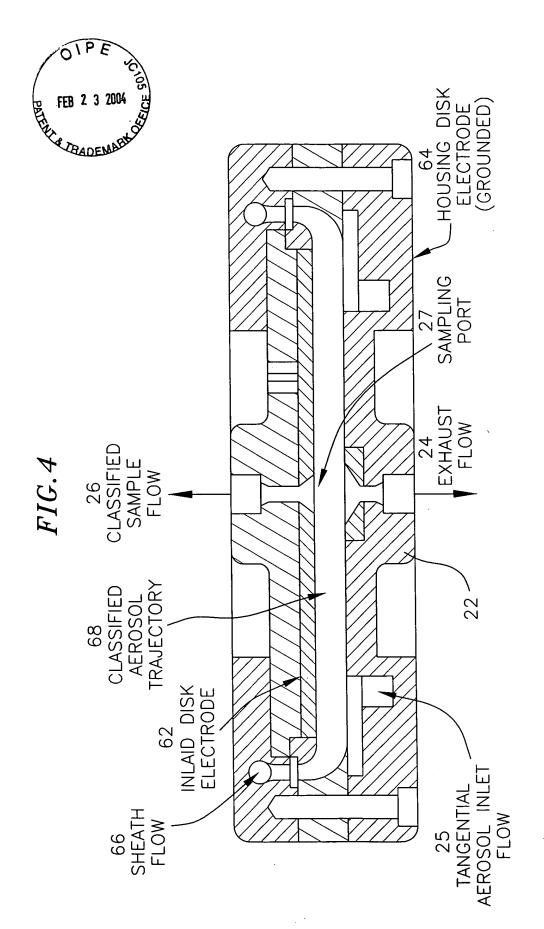


Inventor(s): Richard C. Flagan et al.

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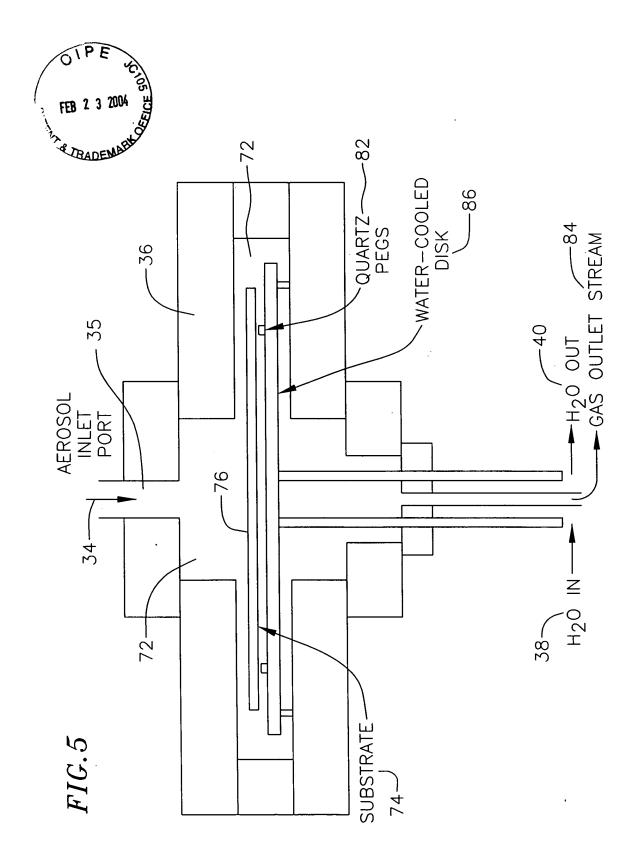
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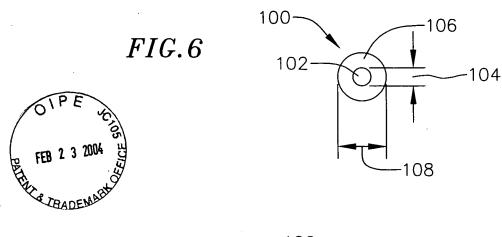


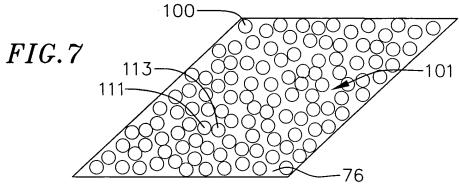
Application No. 09/895,791; Filed: 06/29/2001 Inventor(s): Richard C. Flagan et al.

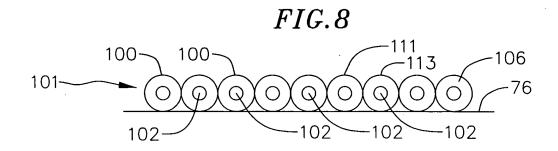
Title: AEROSOL PROCESS FOR FABRICATING DISCONTINUOUS FLOATING GATE MICROELECTRONIC DEVICES

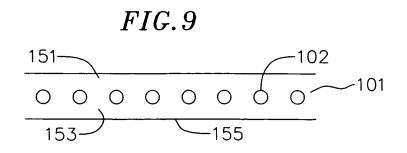
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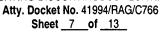




FIG. 10

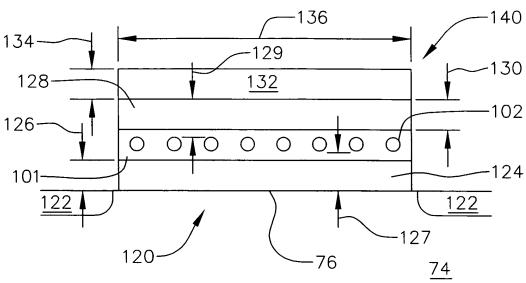
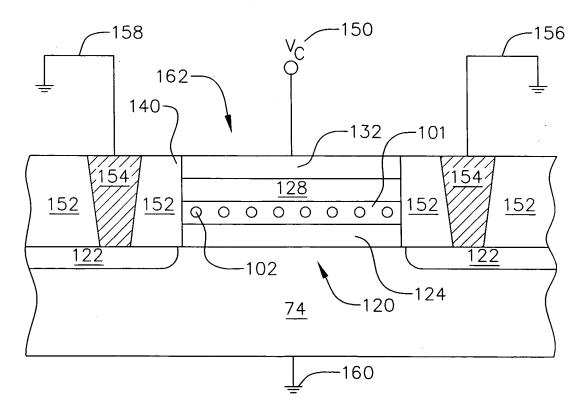


FIG. 11



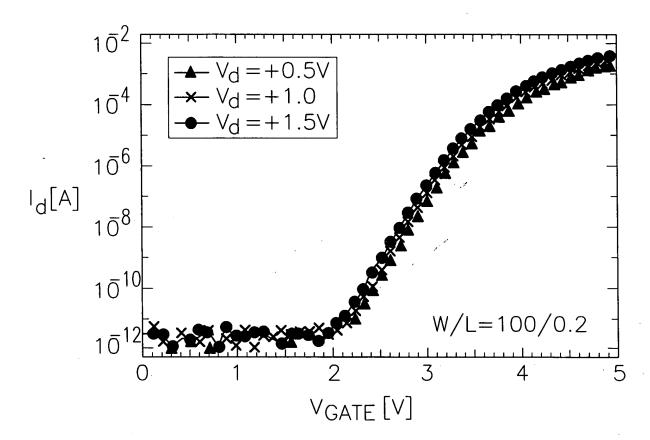
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FIG. 12



SUBTHRESHOLD CHARACTERISTICS OF A $0.2\mu m$ n-TYPE AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET (SUBTHRESHOLD SLOPE=200mV/dec; DIBL=100mV/V).

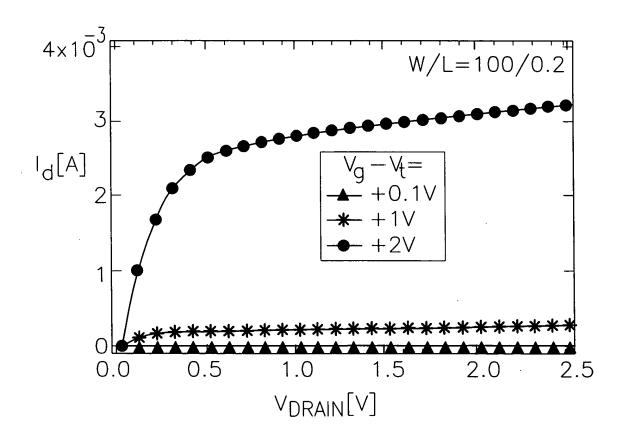
Application No. 09/895,791; Filed: 06/29/2001 Inventor(s): Richard C. Flagan et al.

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FIG. 13



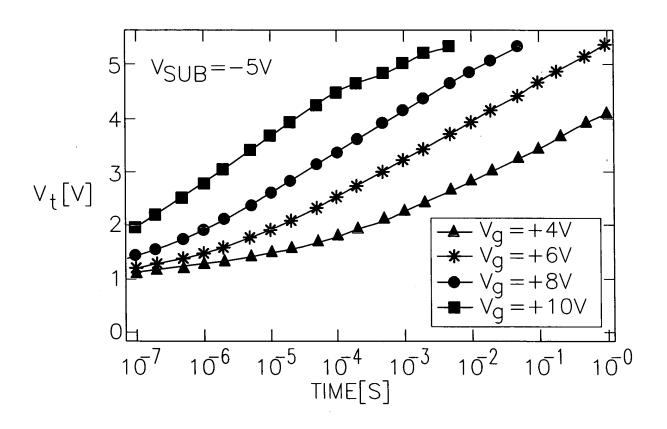
OUTPUT CHARACTERISTICS OF A 0.2 μm AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET; DRIVE CURRENT = $30\mu A/\mu m$

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FIG. 14



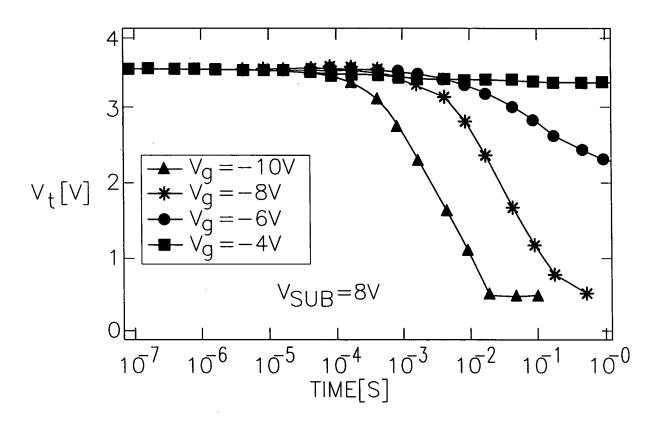
PROGRAMMING TRANSIENTS (UNIFORM FN TUNNELING) OF THE NANOCRYSTAL NVM DEVICE.

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Inventor(s): Richard C. Flagan et al.

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FIG. 15



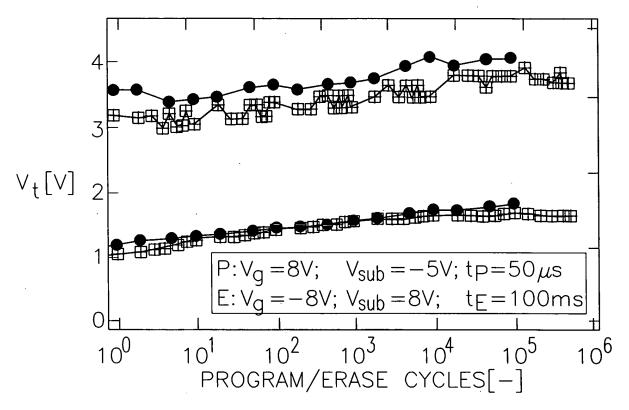
ERASE TRANSIENTS (UNIFORM FN TUNNELING).

Application No. 09/895,791; Filed: 06/29/2001
Inventor(s): Richard C. Flagan et al.

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FIG. 16



ENDURANCE CHARACTERISTIC; ONLY LIMITED WINDOW CLOSURE IS OBSERVED AFTER 10⁵ PROGRAM/ERASE CYCLES.

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FIG. 17

